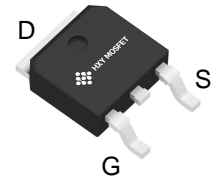




## General Description

The IPD50N10S3L16ATMA2 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness.



TO-252-2L

## General Features

$V_{DS} = 100V$   $I_D = 60A$

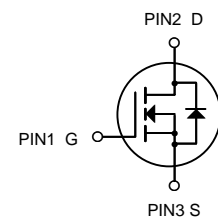
$R_{DS(ON)} < 17m\Omega @ V_{GS}=10V$

## Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications



N-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD50N10S3L16ATMA2	TO252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings at $T_j=25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V <sub>DS</sub>	100	V
Gate source voltage	V <sub>GS</sub>	±20	V
Continuous drain current <sup>1)</sup>	I <sub>D</sub>	60	A
Pulsed drain current <sup>2)</sup>	I <sub>D, pulse</sub>	180	A
Power dissipation <sup>3)</sup>	P <sub>D</sub>	67.5	W
Single pulsed avalanche energy <sup>5)</sup>	E <sub>AS</sub>	80	mJ
Operation and storage temperature	T <sub>stg</sub> , T <sub>j</sub>	-55 to 150	°C
Thermal resistance, junction-case	R <sub>θJC</sub>	1.85	°C/W
Thermal Resistance Junction-Ambient <sup>1</sup>	R <sub>θJA</sub>	45	°C/W



**Electrical Characteristics (T<sub>J</sub>= 25°C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	100	-	-	V	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	T <sub>J</sub> =25°C	-	-	1	μA
			T <sub>J</sub> =100°C	-	-	100	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1	1.7	2.5	V	
Drain-Source on-Resistance <sup>4</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	13.5	17	mΩ	
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	-	17	20		
Forward Transconductance <sup>4</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 20A	-	54	-	S	
<b>Dynamic Characteristics<sup>5</sup></b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz	-	1208	-	pF	
Output Capacitance	C <sub>oss</sub>		-	144	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	11.3	-		
Gate Resistance	R <sub>G</sub>	f = 1MHz	-	1.8	-	Ω	
<b>Switching Characteristics<sup>5</sup></b>							
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A	-	22.7	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	3	-		
Gate-Drain Charge	Q <sub>gd</sub>		-	5	-		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 50V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = 20A	-	9.2	-	ns	
Rise Time	t <sub>r</sub>		-	3.6	-		
Turn-off Delay Time	t <sub>d(off)</sub>		-	25.6	-		
Fall Time	t <sub>f</sub>		-	4.4	-		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A, dI/dt = 100A/μs	-	30	-	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	42	-	nC	
<b>Drain-Source Body Diode Characteristics</b>							
Diode Forward Voltage <sup>4</sup>	V <sub>SD</sub>	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V	-	-	1.2	V	
Continuous Source Current	I <sub>S</sub>	T <sub>C</sub> =25°C	-	-	60	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.4mH, I<sub>AS</sub>=20A.
3. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..



### Typical Characteristics

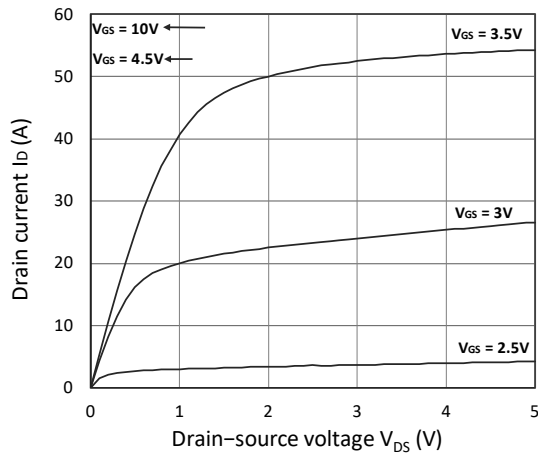


Figure 1. Output Characteristics

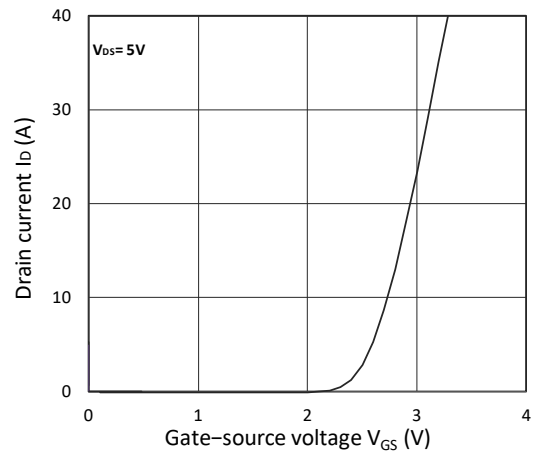


Figure 2. Transfer Characteristics

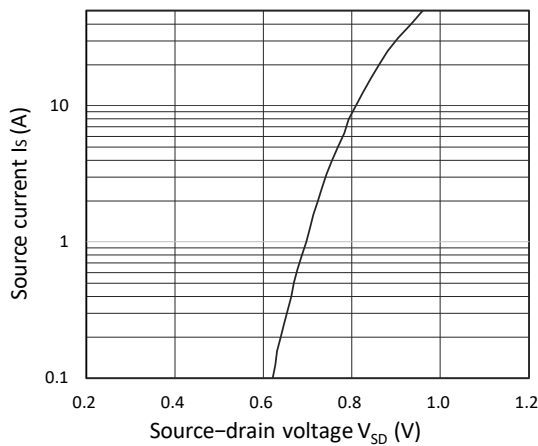


Figure 3. Forward Characteristics of Reverse

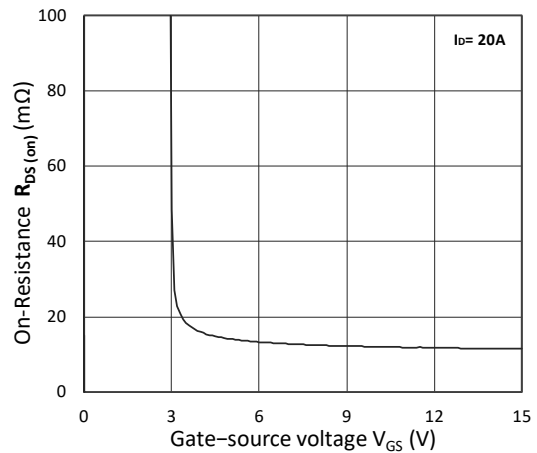


Figure 4.  $R_{DS(on)}$  vs.  $V_{GS}$

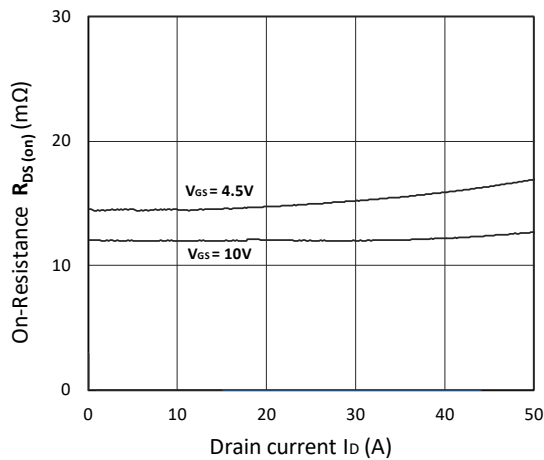


Figure 5.  $R_{DS(on)}$  vs.  $I_D$

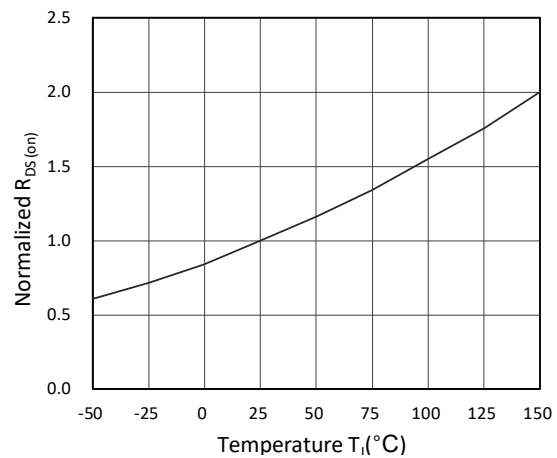


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature

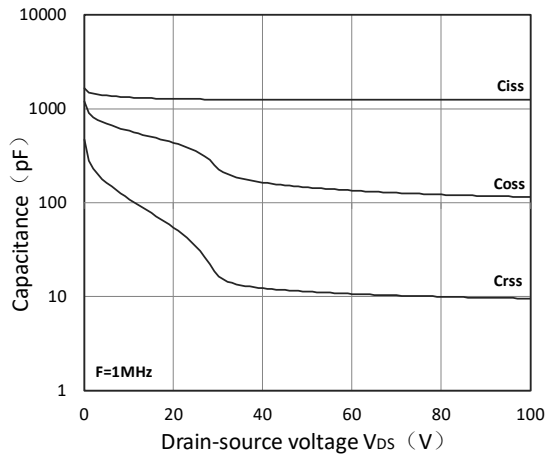


Figure 7. Capacitance Characteristics

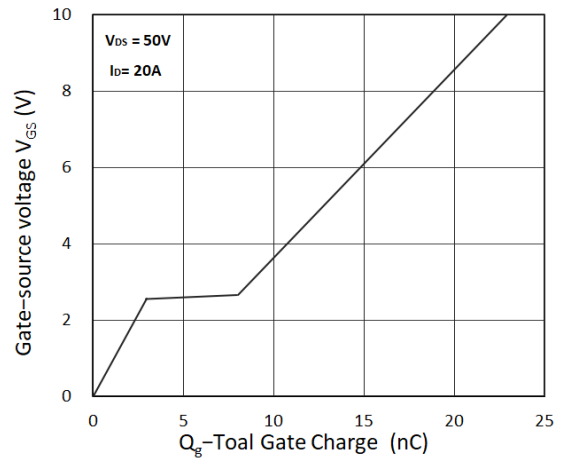


Figure 8. Gate Charge Characteristics

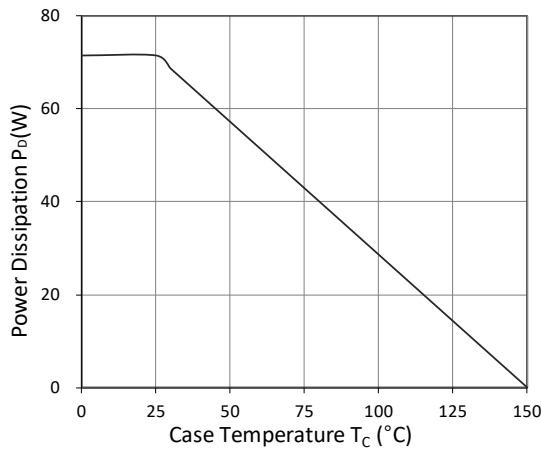


Figure 9. Power Dissipation

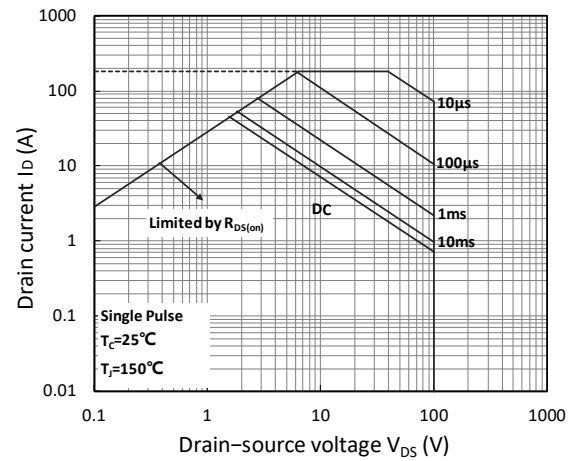


Figure 10. Safe Operating Area

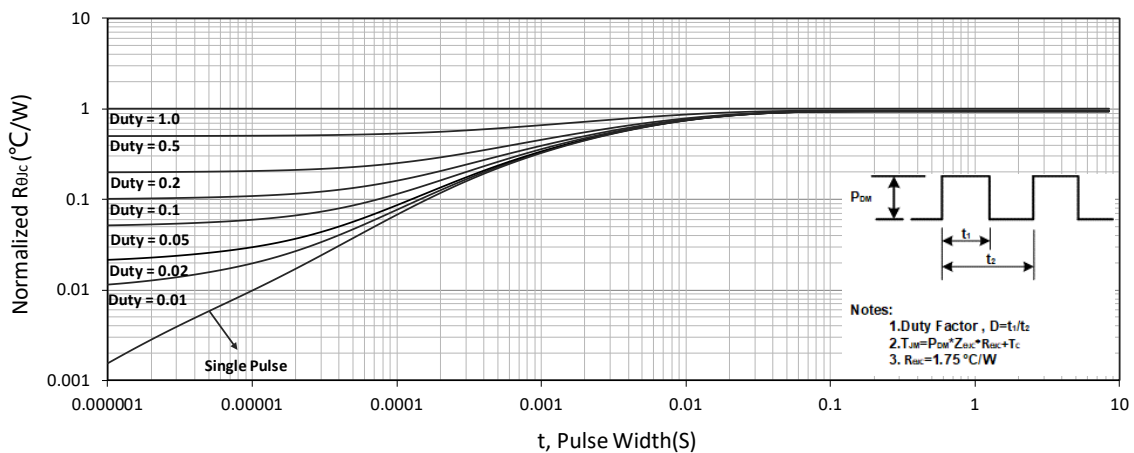


Figure 11. Normalized Maximum Transient Thermal Impedance



### Test Circuit

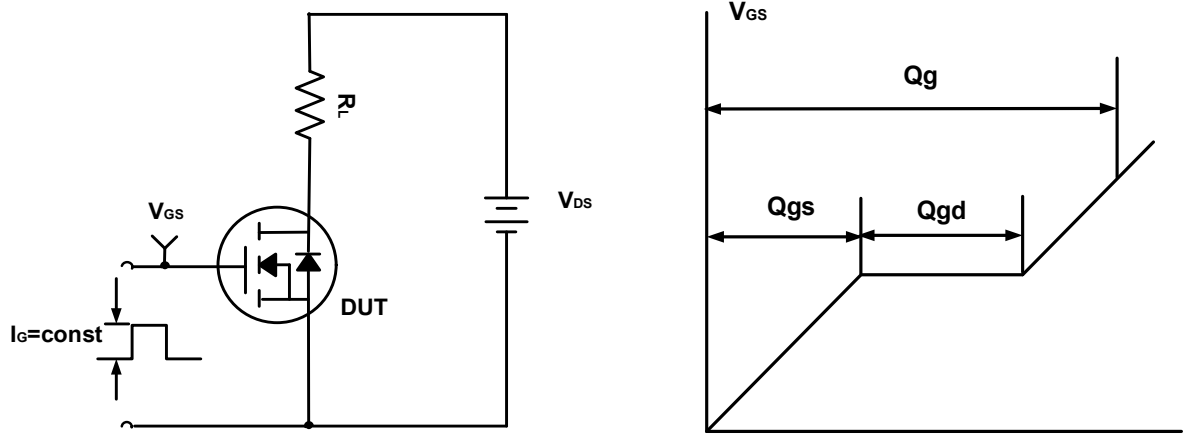


Figure A. Gate Charge Test Circuit & Waveforms

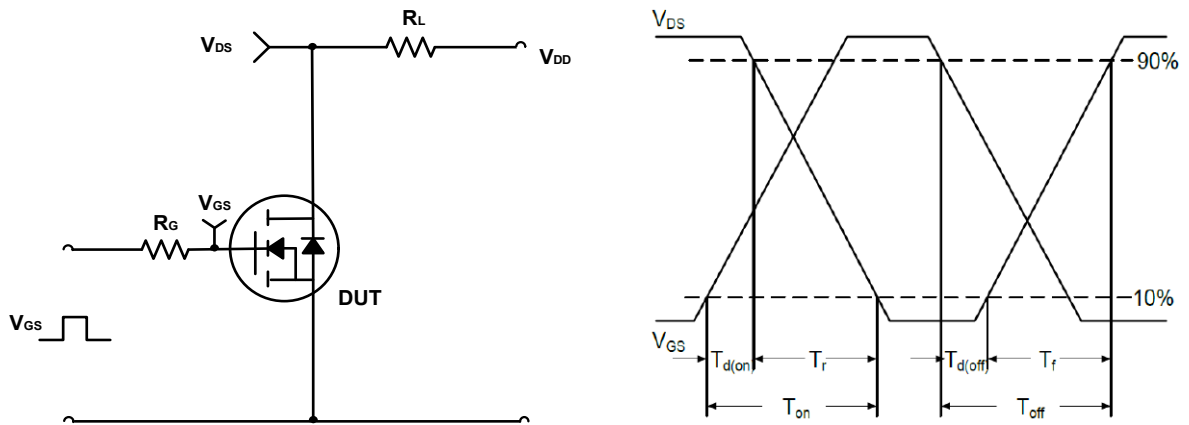


Figure B. Switching Test Circuit & Waveforms

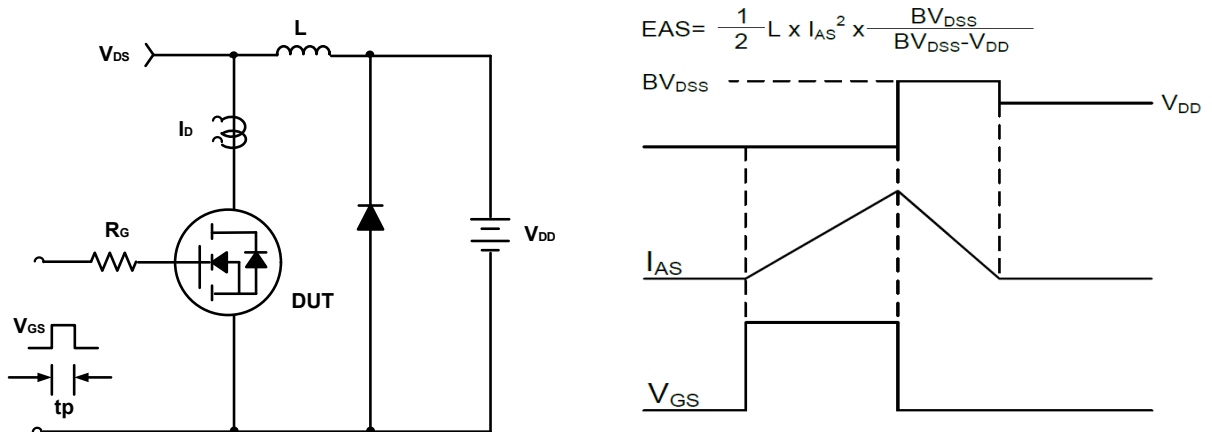
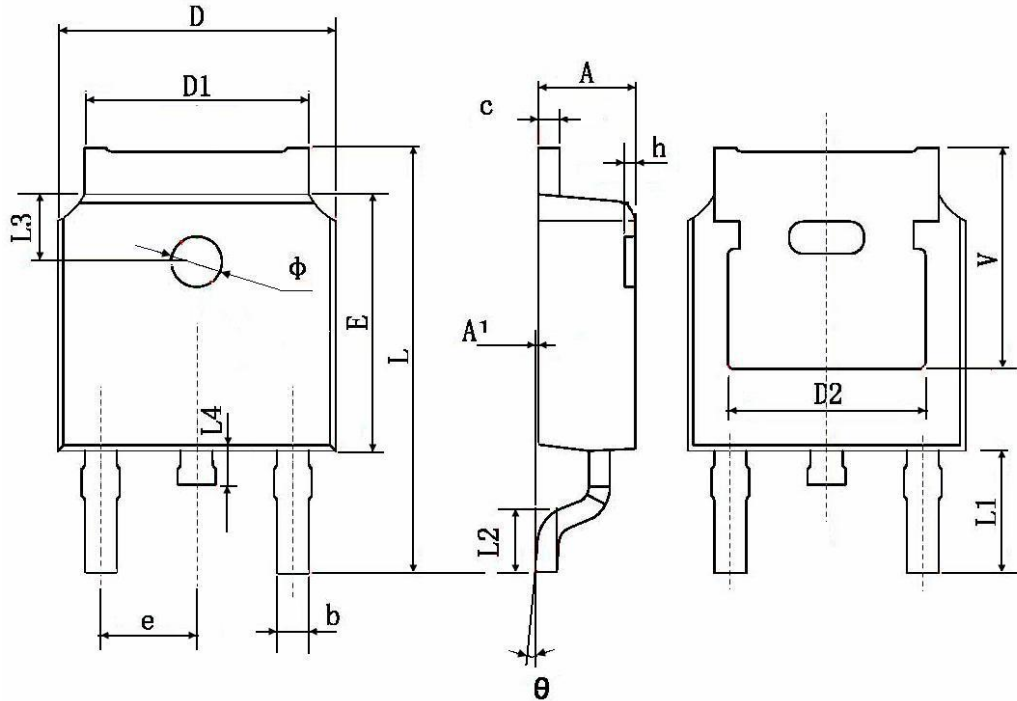


Figure C. Unclamped Inductive Switching Circuit & Waveforms



### TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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